

# Pressure effects on the superconducting thin film $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$

Eunsung Park, Nam Hoon Lee, Won Nam Kang, and Tuson Park\*  
*Department of Physics, Sungkyunkwan University, Suwon 440-746, Korea*

We report electrical resistivity measurements on a high-quality  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  thin film ( $x = 0.4$ ) under pressure. The superconducting transition temperature ( $=39.95$  K) of the optimally-doped thin film shows a dome shape with pressure, reaching a maximal value 40.8 K at 11.8 kbar. The unusually high superconducting transition temperature and its anomalous pressure dependence are ascribed to a lattice mismatch between the  $\text{LaAlO}_3$  substrate and the thin film. The local temperature exponent of the resistivity ( $n = d\ln\Delta\rho/d\ln T$ ) shows a funnel shape around the optimal pressure, suggesting that fluctuations associated with the anomalous normal state are responsible for high-temperature superconductivity.

Since the report of superconductivity in F-doped  $\text{LaFeAsO}_{1-x}\text{F}_x$  [1], Fe-based superconductors have attracted strong interest because of their high superconducting transition temperature (high- $T_c$ ) and the size of the materials space where superconductivity is discovered [2]. Similarity to the cuprate superconductors has been pointed out in that superconductivity is introduced when carriers are induced by hole/electron doping the antiferromagnetic parent compounds and FeAs or FeSe layers are deeply involved in the superconductivity as the CuO layers are in the high- $T_c$  cuprates. It has been recently suggested that the anion height measured from the Fe plane is an important parameter that controls the Fermi surface topology and consequentially the superconductivity [3, 4]. There exists an optimal height ( $h_m$ ) where the superconducting transition temperature is a maximum and  $T_c$  decreases as the height departs from  $h_m$ .

Thin films grown on different types of single crystal substrates may manifest uniaxial pressure effects because a lattice mismatch relative to the substrate leads to either contraction or expansion of the film and a change in the anion height [5]. Iida *et al.* reported that  $T_c$  of a  $\text{Ba}(\text{Fe},\text{Co})_2\text{As}_2$  (Co-Ba122) thin film changes from 16.2 to 24.5 K with increasing  $c/a$ , where the out-of-plane lattice parameter  $c$  decreases with an increase of the in-plane lattice constant  $a$  for different types of substrates [6]. Bellingeri *et al.* found that the  $T_c$  of 21 K for a  $\text{FeSe}_{0.5}\text{Te}_{0.5}$  thin film is significantly higher than 16.2 K for a bulk crystal, suggesting that strain effects in thin films may provide a way to raise  $T_c$  [7].

Despite the ever growing interest in thin film studies, however, the high volatility of the doping elements often makes it difficult to fabricate thin films of the iron-pnictide superconductors. An electron-doped  $\text{BaFe}_{2-x}\text{Co}_x\text{As}_2$  thin film with  $T_c \approx 20$  K has been synthesized with relative ease because cobalt atoms have a lower vapor pressure, while a hole-doped  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  thin film has been fabricated only recently by overcoming the technical difficulty of a large difference in the

vapor pressures of constituent elements [8–13]. Lee *et al.* recently reported successful synthesis of a thin film of  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$ , where  $T_c$  is as high as 40 K [12]. Here we report for the first time the dependence of superconducting properties on externally applied pressure for a  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film. Unlike single crystalline compounds,  $T_c$  of the optimally doped thin film does not decrease monotonically with pressure but rather shows a dome centered around 11.8 kbar ( $=P_c$ ). The electrical resistivity of the film in the normal state shows an anomalous power-law temperature dependence under pressure. The local temperature exponent of the resistivity shows a funnel shape above the optimal pressure  $P_c$ , suggesting that fluctuations relevant to anomalous normal state properties are responsible for high- $T_c$  superconductivity in the Fe-pnictides superconductors.

Optimally doped thin films of  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  were grown on  $\text{LaAlO}_3$  (001) substrates by a pulsed laser deposition (PLD) method, and X-ray diffraction measurements showed that films with a tetragonal structure grow preferentially along the crystalline  $c$ -axis [12]. The lattice parameters determined from a least-squares refinement of the x-ray pattern are  $a = 3.9068$  Å and  $c = 13.4037$  Å, where  $c/a = 3.4308$  is slightly larger than that of optimally doped bulk crystals ( $=3.40$ ) [14]. Electrical resistivity of the K-doped  $\text{BaFe}_2\text{As}_2$  thin film was measured by a standard four-probe technique in a closed cycle refrigerator (CCR). A clamp-type Be/Cu hybrid cell with a NiCrAl alloy insert was used for resistivity measurements up to 28.2 kbar, and a change in the resistivity of an annealed manganin wire was used as a pressure monitor at room temperature [15].

Figure 1 shows the temperature dependence of the in-plane electrical resistivity  $\rho$  of a thin film of  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  under pressure. As shown in the inset, the onset temperature of a superconducting (SC) phase transition ( $T_c^{\text{onset}}$ ), which is defined as the deviation point from a linear temperature dependence of the resistivity in the normal state (dotted line), is 39.95 K at ambient pressure, the highest for optimally doped films on a  $\text{LaAlO}_3$  (LAO) substrate. The SC transition width, the difference between a 10 % to 90 % drop of the normal state resistivity at  $T_c^{\text{onset}}$ , is 1.30 K and the residual resistivity ratio (RRR)  $\rho(300\text{ K})/\rho(0\text{ K})$  at 1 bar is

\*tp8701@skku.edu

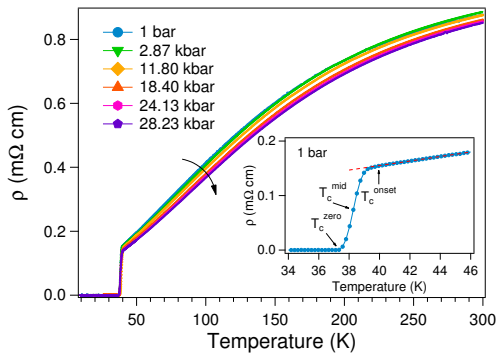


FIG. 1: (color online) Electrical resistivity of a  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film deposited on a  $\text{LaAlO}_3$  (LAO) substrate under pressure. The arrow indicates a pressure increase from 1 bar to 28.23 kbar. Inset: The resistivity at ambient pressure is displayed near SC transition temperature.

38, indicating the high quality of this thin film. Here,  $\rho(0 \text{ K}) = 0.023 \text{ m}\Omega\text{cm}$  is an extrapolated value from the  $\rho = \rho(0 \text{ K}) + AT^{1.2}$  dependence in the normal state. Externally applied pressure monotonically reduces the resistivity in the normal state because of an increased overlap among adjacent ligand orbitals under pressure:  $\rho$  at 41 K and 300 K decreases at a rate of  $-0.6$  and  $-1.1 \times 10^{-3} \text{ m}\Omega\text{cm}/\text{kbar}$ , respectively.

The pressure evolution of superconducting transition temperatures is plotted in Fig. 2, where  $T_c^{\text{onset}}$ ,  $T_c^{\text{mid}}$ , and  $T_c^{\text{zero}}$  represents the onset, midpoint and zero-resistance transition temperatures, respectively (see the inset of Fig. 1).  $T_c^{\text{onset}}$  gradually increases from 39.95 K at 1 bar to 40.8 K at 11.80 kbar and then decreases with further increasing pressure, showing a dome-shaped superconducting phase centered on the optimal pressure  $P_c (=11.80 \text{ kbar})$ . Such pressure effects on the thin film are unexpected because  $T_c$  of single crystals with similar stoichiometry is continuously suppressed with pressure [16, 17]. For  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  bulk crystals, the  $c/a$  ratio almost linearly increases with potassium concentration  $x$  and is approximately 3.410 for an optimally K-doped compound ( $x = 0.4$ ) [14]. The ratio  $c/a = 3.4308$  observed in our thin film corresponds to an overdoped concentration  $x = 0.46$  for a bulk crystal, ruling out the possibility that the thin film on LAO is underdoped. In addition, the  $T_c$  of 39.95 K is too high for any underdoped compound. For comparison,  $T_c$  of an optimally doped bulk crystal is 38 K [14, 18].

The unusual pressure dependence of the optimally doped thin film may be ascribed to a high  $c/a$  ratio that arises from a lattice mismatch between the film and LAO substrate. It has been reported that the  $c/a$  ratio of a  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film deposited on  $\text{Al}_2\text{O}_3$  (AO) and  $\text{LaAlO}_3$  (LAO) substrates is 3.4028 and 3.4308, respectively [12]. The superconducting transition temperature of a film on a AO substrate is almost 1 K higher than that on a LAO substrate, indicating that the anion height of a

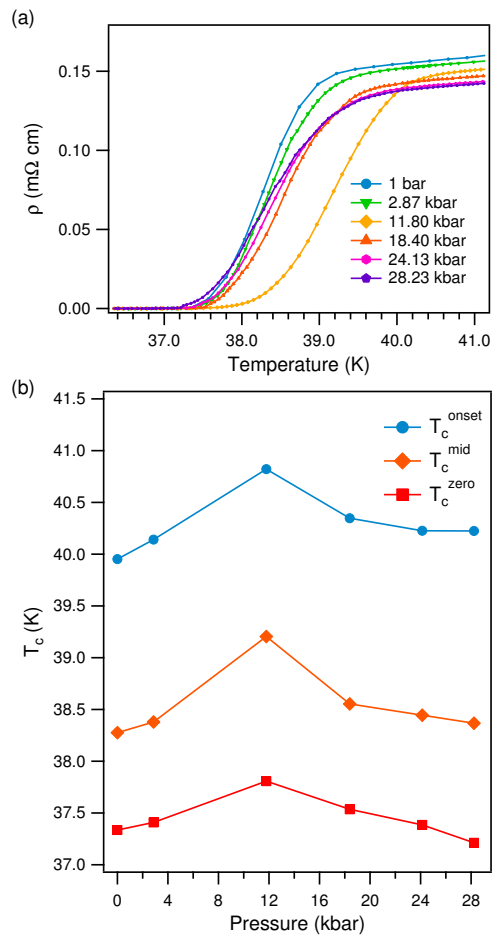


FIG. 2: (color online). (a) Pressure dependence of the resistivity of a  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  ( $x = 0.4$ ) thin film near its superconducting transition temperature. (b) Superconducting transition temperature vs pressure phase diagram, where  $T_c^{\text{onset}}$ ,  $T_c^{\text{mid}}$ , and  $T_c^{\text{zero}}$  represent the onset, midpoint, and  $\rho = 0$  SC transition temperatures, respectively.

AO-film is close to the optimal height  $h_m$ , while the anion height of a film on LAO is slightly larger than  $h_m$ . Lattice constants of the LAO substrate are almost independent of hydrostatic pressure and isotropic among crystalline axes: the relative change in lattice constants being only 0.55% at 32.1 kbar [19]. In contrast, the lattice constants of a tetragonal  $\text{BaFe}_2\text{As}_2$  single crystal are compressed significantly both along the crystalline  $a$ - and  $c$ -axes with pressure: at 32.1 kbar, the lattice constant  $a$  and  $c$  decreases by 1.03 and 2.02%, respectively [20]. When the thin film of  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  is under hydrostatic pressure, it effectively experiences a uniaxial pressure along the  $c$ -axis because the change in the lattice constant  $a$  is almost negligible because it is pinned to the substrate lattice, while the lattice constant along the  $c$ -axis is compressed as easily as in a single crystal. Consequently, hydrostatic pressure acts as an effective uniaxial pressure along the  $c$ -axis and controls the anion height of the film to the optimal  $h_m$  at 11.8 kbar, therefore making

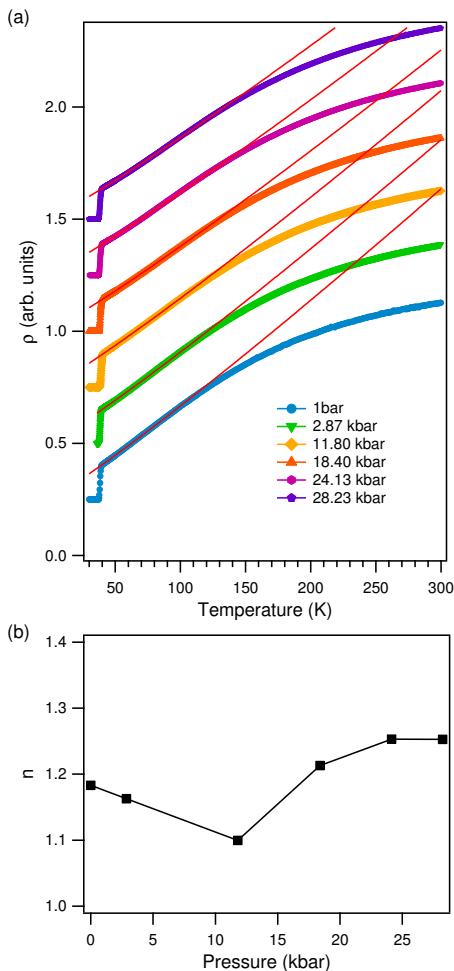


FIG. 3: (color online). (a) Temperature dependence of the resistivity of  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  ( $x = 0.4$ ) under pressure and a least-squares fit of  $\rho = \rho_0 + AT^n$  (solid lines). The resistivity under pressure is shifted rigidly upwards for clarity. (b) Pressure dependence of the resistivity coefficient  $n$  of the power-law form.

the dome-shaped SC phase under pressure.

Figure 3(a) displays the temperature dependence of the resistivity of the  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film on the LAO substrate for several pressures. Regardless of the applied pressure, a power-law form of  $\rho = \rho_0 + AT^n$  best describes the normal state resistivity over an extended temperature range above  $T_c$ , where the exponent  $n$  of the resistivity changes between 1.1 and 1.25 under pressure (see Fig. 3(b)). The anomalous temperature exponent  $n$  is consistent with previous work on single crystals that reported a gradual change of  $n$  from 2 (undoped) to 1 (at optimal potassium doping) [21].

Figure 4 plots the local temperature exponent of the resistivity ( $n = d\ln\Delta\rho/d\ln T$ ) in  $T$ - $P$  phase space, where  $\Delta\rho = \rho(T) - \rho(T = 0\text{K})$ . The local exponent  $n$  is less than 1.25 below 100 K in the measured pressure range, which is comparable to the results via a global

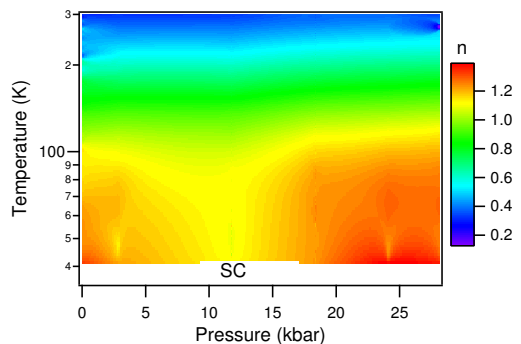


FIG. 4: (color online). Evolution of the local temperature exponent  $n$  of a  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film is plotted in the temperature-pressure phase space. The local exponent is defined as  $n = d\ln\Delta\rho/d\ln T$ , where  $\Delta\rho = \rho(T) - \rho(T = 0\text{K})$ .

fit of the resistivity (see Fig. 3(a)). The local analysis, however, reveals a delicate topology in the resistivity exponent, showing a funnel shape with  $n = 1.1$  above the optimal pressure. Even though the optimally doped  $\text{Ba}_{0.6}\text{K}_{0.4}\text{Fe}_2\text{As}_2$  thin film at 1 bar is probably in the vicinity of a quantum critical point (QCP), external pressure sensitively tunes the film right to the QCP where the associated quantum fluctuations diverge. A similar analysis based on the local resistivity exponent has been performed to show evidence for quantum critical behavior in other iron-pnictides superconductors as a function of chemical doping [22], which inherently incur disorder whose effects on the electron scattering may change with doping concentration. In this work, the K-doped Ba122 thin film with  $x = 0.4$  was sensitively tuned to a critical point via pressure, thus allowing us to study the quantum critical behavior without incurring additional disorder. A funnel shaped resistivity exponent above an optimal pressure has been also reported in the pressure-induced heavy fermion superconductor  $\text{CeRhIn}_5$  [23]. Future characterization of the spectra of quantum fluctuations that are pertinent to the high SC transition temperature in iron-pnictides superconductors requires simultaneous tuning of such external parameters as pressure, magnetic field, and low temperatures.

We fabricated  $\text{Ba}_{1-x}\text{K}_x\text{Fe}_2\text{As}_2$  ( $x = 0.4$ ) thin films on a  $\text{LaAlO}_3$  substrate, where  $T_c$  is 39.95 K. The sharp superconducting phase transition ( $\Delta T_c = 1.30\text{K}$ ) and large residual resistivity ratio (RRR = 38) indicate high quality of the film. Unlike single crystals with similar stoichiometry,  $T_c$  of the thin film with optimal potassium concentration gradually increases to 40.8 K at 11.8 kbar ( $P_c$ ) and decreases with further increasing pressure, showing a dome shape. The unusual pressure dependence of  $T_c$  is ascribed to a lattice mismatch between the LAO substrate and thin film, where applied hydrostatic pressure effectively acts as uniaxial pressure along the crystalline  $c$ -axis of the film. The local temperature exponent of the resistivity reveals a funnel-shaped

topology surrounding the optimal pressure  $P_c$ , indicating the presence of a quantum critical point where the normal-state properties are dominated by the associated quantum fluctuations.

This work was supported by Mid-career Researcher

Program through NRF grant funded by the Ministry of Education, Science & Technology (MEST) (No. 2010-0029136). TP acknowledges support from the NRF grant (No. 2010-0026762 & 2011-0021645).

- 
- [1] Y. Kamihara, T. Watanabe, M. Hirano, and H. Hosono, *J. Am. Chem. Soc.* **130**, 3296 (2008).
- [2] G. R. Stewart, *Rev. Mod. Physics*, **83**, 1589 (2011).
- [3] C.-H. Lee, A. Iyo, H. Eisaki, H. Kito, M. T. Fernandez-Diaz, T. Ito, K. Kihou, H. Matsuhata, M. Braden, and K. Yamada, *J. Phys. Soc. Jpn.* **77** 083704 (2008).
- [4] K. Kuroki, *J. Phys. Chem. Solids* **72**, 307 (2011).
- [5] H. Hiramatsu, T. Katase, T. Kamiya, and H. Hosono, *J. Phys. Soc. Jpn.* **81** 011011 (2012).
- [6] K. Iida, J. Hnisch, S. Trommler, V. Matias, S. Haindl, F. Kurth, I. L. del Pozo, R. Hhne, M. Kitzun, J. Engelmann, L. Schultz, and B. Holzapfel, *Appl. Phys. Lett.* **95**, 192501 (2009).
- [7] E. Bellingeri, I. Pallicchi, R. Buzio, A. Gerbi, D. Marr, M. R. Cimberle, M. Tropeano, M. Putti, A. Palenzona, and C. Ferdeghini, *Appl. Phys. Lett.* **96**, 102512 (2010).
- [8] S. Lee, J. Jiang, J. D. Weiss, C. M. Folkman, C. W. Bark, C. Tarantini, A. Xu, D. Abraimov, A. Polyanskii, C. T. Nelson, Y. Zhang, S. H. Baek, H. W. Jang, A. Yamamoto, F. Kametani, X. Q. Pan, E. E. Hellstrom, A. Gurevich, C. B. Eom, and D. C. Larbalestier, *Appl. Phys. Lett.* **95**, 212505 (2009).
- [9] S. Lee, J. Jiang, Y. Zhang, C. W. Bark, J. D. Weiss, C. Tarantini, C. T. Nelson, H. W. Jang, C. M. Folkman, S. H. Baek, A. Polyanskii, D. Abraimov, A. Yamamoto, J. W. Park, X. Q. Pan, E. E. Hellstrom, D. C. Larbalestier, and C. B. Eom, *Nat. Mater.* **9**, 397 (2010).
- [10] K. Iida, S. Haindl, T. Thersleff, J. Hnisch, F. Kurth, M. Kitzun, R. Hhne, I. Munch, L. Schultz, B. Holzapfel, and R. Heller, *Appl. Phys. Lett.* **97**, 172507 (2010).
- [11] T. Katase, H. Hiramatsu, T. Kamiya, and H. Hosono, *Appl. Phys. Express* **3**, 063101 (2010).
- [12] N. H. Lee, S.-G. Jung, D. H. Kim, and W. N. Kang, *Appl. Phys. Lett.* **96**, 202505 (2010).
- [13] S. Takeda, S. Ueda, T. Yamagishi, S. Agatsuma, S. Takano, A. Mitsuda, and M. Naito, *Appl. Phys. Express* **3**, 093101 (2010).
- [14] M. Rotter, M. Pangerl, M. Tegel, and D. Johrendt, *Angew. Chem.* **47**, 7949 (2008).
- [15] L. H. Dmowski and E. Litwin-Staszewska, *Meas. Sci. Technol.* **10** 343 (1999).
- [16] T. Yamazaki, N. Takeshita, K. Kondo, R. Kobayashi, Y. Yamada, H. Fukazawa, Y. Kohori, P. M. Shirage, K. Kihou, H. Kito, H. Eisaki, and A. Iyo, *J. Phys.:Conf. Series* **215**, 012041 (2010).
- [17] M. S. Torikachvili, S. L. Bud'ko, N. Ni, and P. C. Canfield, *Phys. Rev. B* **78**, 104527 (2008).
- [18] H. Luo, Z. Wang, H. Yang, P. Cheng, X. Zhu, and H.-H. Wen, *Supercond. Sci. Technol.* **21**, 125014 (2008).
- [19] J. Zhao, N. L. Ross, and R. J. Angel, *J. Phys.: Condens. Matter* **16**, 8763 (2004).
- [20] S. A. J. Kimber, A. Kreyssig, Y.-Z. Zhang, H. O. Jeschke, R. Valent, F. Yokaichiya, E. Colombier, J. Yan, T. C. Hansen, T. Chatterji, R. J. McQueeney, P. C. Canfield, A. I. Goldman, and D. N. Argyriou, *Nature Mat.* **8**, 471 (2009).
- [21] B. Shen, H. Yang, Z.-S. Wang, F. Han, B. Zeng, L. Shan, C. Ren, and H.-H. Wen, *Phys. Rev. B* **84**, 184512 (2011).
- [22] S. Kasahara, T. Shibauchi, K. Hashimoto, K. Ikada, S. Tonegawa, R. Okazaki, H. Shishido, H. Ikeda, H. Takeya, K. Hirata, T. Terashima, and Y. Matsuda, *Phys. Rev. B* **81**, 184519 (2010).
- [23] T. Park, V. A. Sidorov, F. Ronning, J.-X. Zhu, Y. Tokiwa, H. Lee, E. D. Bauer, R. Movshovich, J. L. Sarrao, and J. D. Thompson, *Nature* **456**, 366 (2008).